



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

0755-83047638

ysbdt@szyoushang.cn

www.szyoushang.cn



企业微信二维码



企业QQ二维码

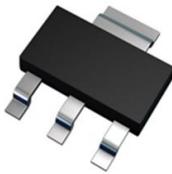
## Features

- $BV_{CEO} > 100V$
- $I_C = 1A$  High Continuous Current
- $I_{CM} = 2A$  Peak Pulse Current
- Low Saturation Voltage
- Complementary PNP Type: NK-FZT593

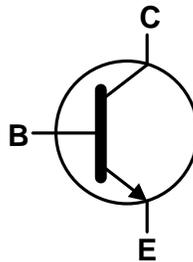
## Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound; UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 Ⓢ
- Weight: 0.112 grams (Approximate)

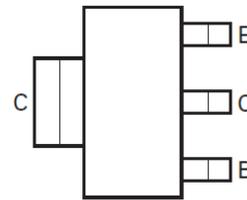
SOT223



Top View



Device Symbol



Top View  
Pin-Out

### Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic               | Symbol           | Value | Unit |
|------------------------------|------------------|-------|------|
| Collector-Base Voltage       | V <sub>CB0</sub> | 120   | V    |
| Collector-Emitter Voltage    | V <sub>CEO</sub> | 100   | V    |
| Emitter-Base Voltage         | V <sub>EBO</sub> | 7     | V    |
| Continuous Collector Current | I <sub>C</sub>   | 1     | A    |
| Base Current                 | I <sub>B</sub>   | 200   | mA   |
| Peak Pulse Current           | I <sub>CM</sub>  | 2     | A    |

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

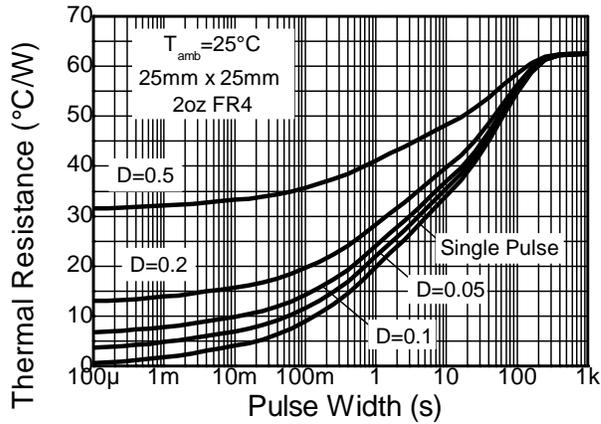
| Characteristic                          | Symbol                            | Value            | Unit |  |
|---|-----------------------------------|------------------|------|--|
| Power Dissipation                       | (Note 6)                          | 3.0              | W    |  |
|   | (Note 7)                          | 2.0              |      |  |
|   | (Note 8)                          | 1.6              |      |  |
|   | (Note 9)                          | 1.2              |      |  |
| Thermal Resistance, Junction to Ambient | (Note 6)                          | 41.7             | °C/W |  |
|   | (Note 7)                          | 62.5             |      |  |
|   | (Note 8)                          | 78.1             |      |  |
|   | (Note 9)                          | 104              |      |  |
| Thermal Resistance Junction to Lead     | (Note 10)                         | R <sub>θJL</sub> | 19.4 |  |
| Operating and Storage Temperature Range | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150      | °C   |  |

### ESD Ratings (Note 11)

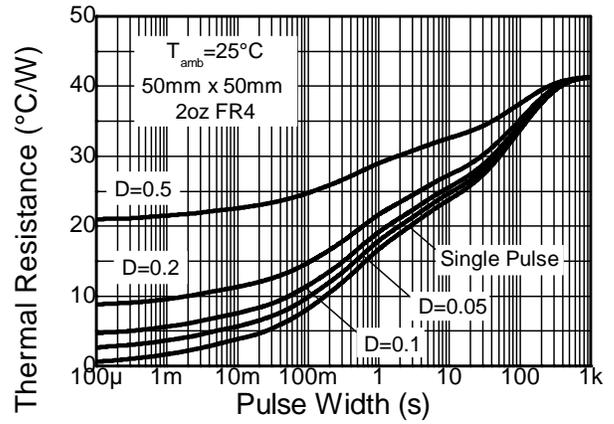
| Characteristic                             | Symbol  | Value | Unit | JEDEC Class |
|--|---------|-------|------|-------------|
| Electrostatic Discharge - Human Body Model | ESD HBM | 4,000 | V    | 3A          |
| Electrostatic Discharge - Machine Model    | ESD MM  | 400   | V    | C           |

- Notes:
6. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
  7. Same as Note 6, except the device is mounted on 25mm x 25mm 2oz copper.
  8. Same as Note 6, except the device is mounted on 25mm x 25mm 1oz copper.
  9. Same as Note 6, except the device is mounted on minimum recommended pad layout.
  10. Thermal resistance from junction to solder-point (at the end of the collector lead).
  11. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

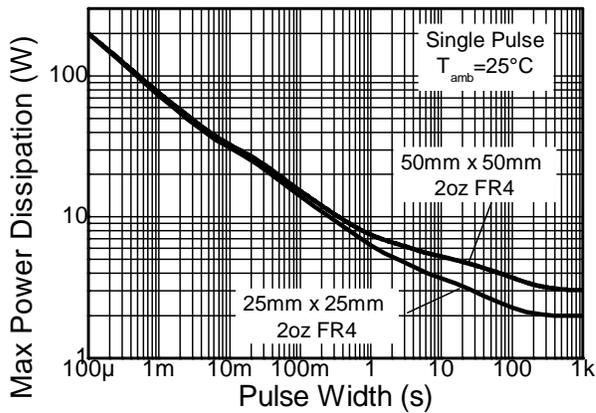
## Thermal Characteristics and Derating Characteristics



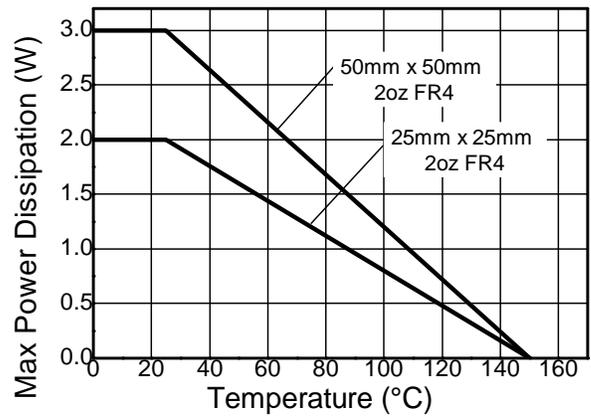
**Transient Thermal Impedance**



**Transient Thermal Impedance**



**Pulse Power Dissipation**



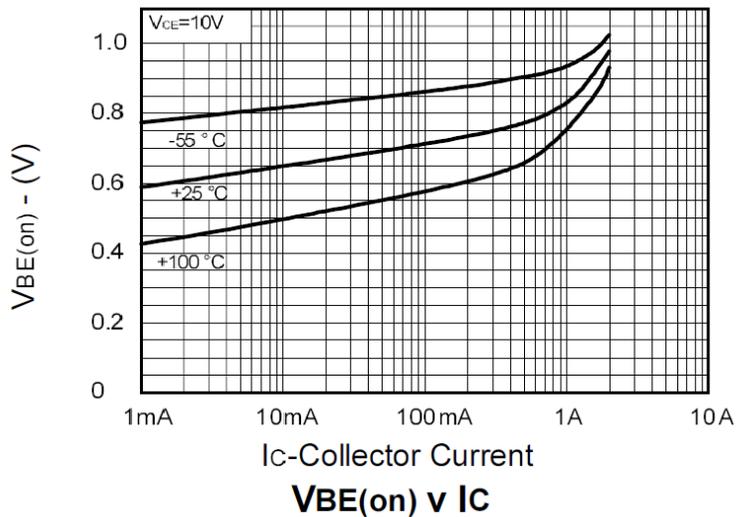
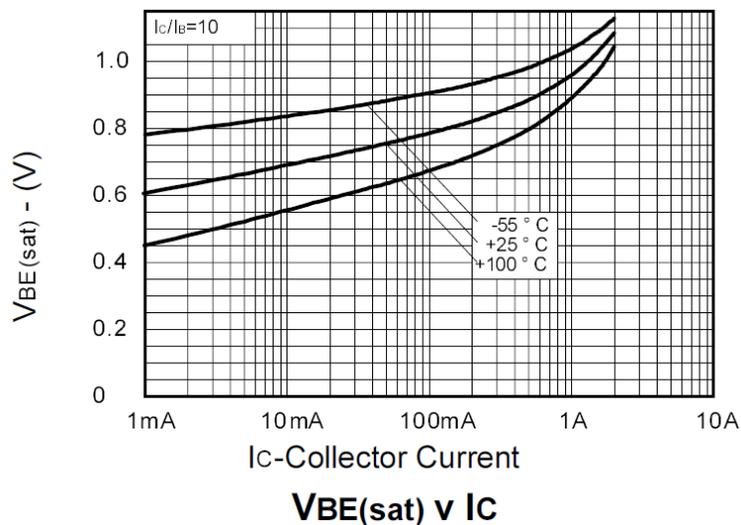
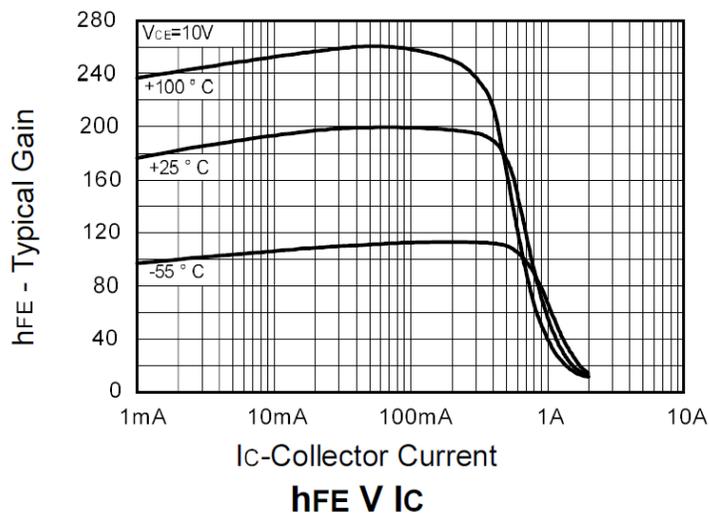
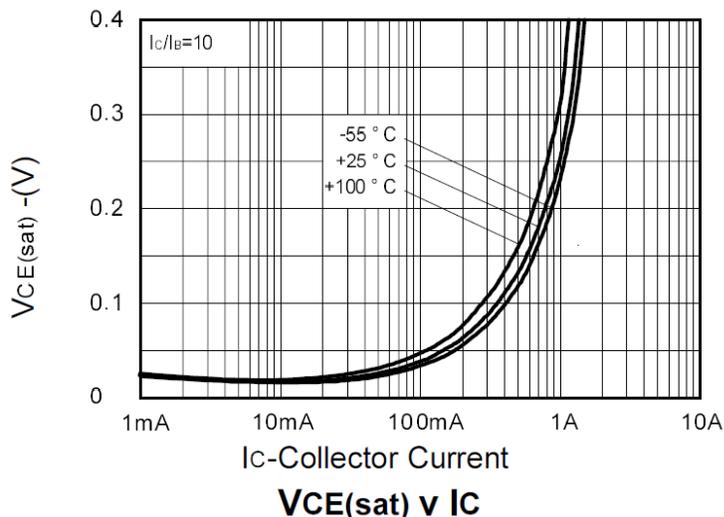
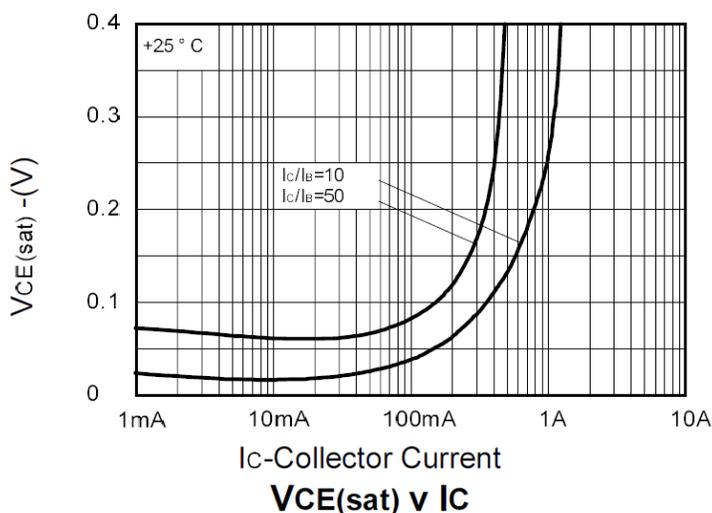
**Derating Curve**

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

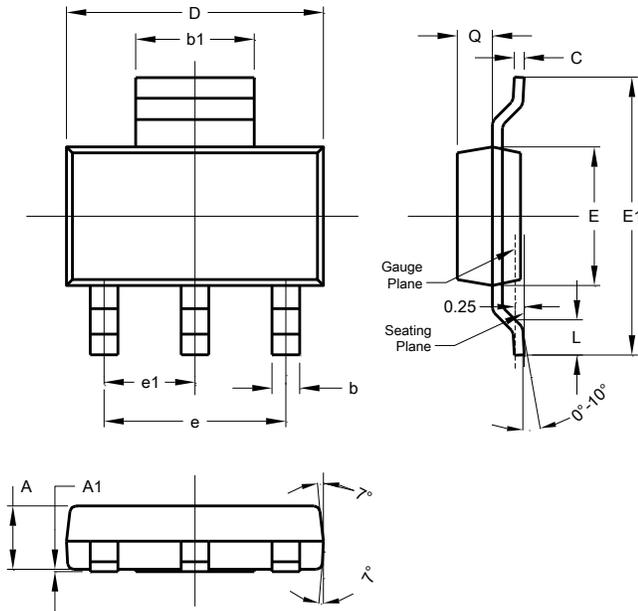
| Characteristic                                 | Symbol        | Min                    | Typ              | Max                | Unit | Test Condition  |
|--|---------------|------------------------|------------------|--------------------|------|---|
| Collector-Base Breakdown Voltage               | $BV_{CBO}$    | 120                    | –                | –                  | V    | $I_C = 100\mu A$  |
| Collector-Emitter Breakdown Voltage (Note 12)  | $BV_{CEO}$    | 100                    | –                | –                  | V    | $I_C = 10mA$  |
| Emitter-Base Breakdown Voltage                 | $BV_{EBO}$    | 5                      | –                | –                  | V    | $I_E = 100\mu A$  |
| Collector Cut-Off Current                      | $I_{CBO}$     | –                      | –                | 100                | nA   | $V_{CB} = 100V$   |
| Collector Cut-Off Current                      | $I_{CES}$     | –                      | –                | 100                | nA   | $V_{CE} = 100V$   |
| Emitter Cut-Off Current                        | $I_{EBO}$     | –                      | –                | 100                | nA   | $V_{EB} = 4V$   |
| Collector-Emitter Saturation Voltage (Note 12) | $V_{CE(sat)}$ | –                      | –                | 0.3<br>0.6         | V    | $I_C = 500mA, I_B = 50mA$<br>$I_C = 1A, I_B = 100mA$  |
| Base-Emitter Saturation Voltage (Note 12)      | $V_{BE(sat)}$ | –                      | –                | 1.15               | V    | $I_C = 1A, I_B = 100mA$   |
| Base-Emitter Turn-On Voltage (Note 12)         | $V_{BE(on)}$  | –                      | –                | 1.0                | V    | $I_C = 1A, V_{CE} = 10V$  |
| DC Current Gain (Note 12)                      | $h_{FE}$      | 100<br>100<br>80<br>30 | –<br>–<br>–<br>– | –<br>300<br>–<br>– | –    | $I_C = 1mA, V_{CE} = 10V$<br>$I_C = 250mA, V_{CE} = 10V$<br>$I_C = 500mA, V_{CE} = 10V$<br>$I_C = 1A, V_{CE} = 10V$ |
| Current Gain-Bandwidth Product                 | $f_T$         | 150                    | –                | –                  | MHz  | $V_{CE} = 10V, I_C = 50mA$<br>$f = 100MHz$  |
| Output Capacitance                             | $C_{obo}$     | –                      | –                | 10                 | pF   | $V_{CB} = 10V, f = 1MHz$  |

 Note: 12. Measured under pulsed conditions. Pulse width  $\leq 300\mu s$ . Duty cycle  $\leq 2\%$ .

**Typical Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

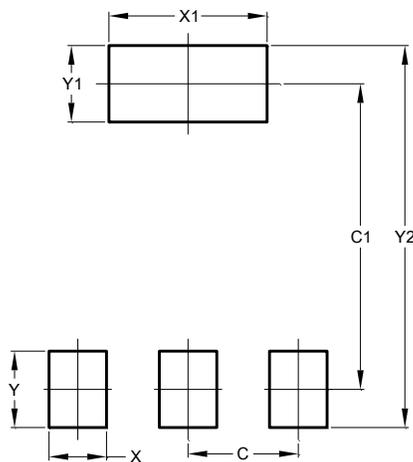


### Package Outline Dimensions



| SOT223               |       |      |      |
|----------------------|-------|------|------|
| Dim                  | Min   | Max  | Typ  |
| A                    | 1.55  | 1.65 | 1.60 |
| A1                   | 0.010 | 0.15 | 0.05 |
| b                    | 0.60  | 0.80 | 0.70 |
| b1                   | 2.90  | 3.10 | 3.00 |
| C                    | 0.20  | 0.30 | 0.25 |
| D                    | 6.45  | 6.55 | 6.50 |
| E                    | 3.45  | 3.55 | 3.50 |
| E1                   | 6.90  | 7.10 | 7.00 |
| e                    | -     | -    | 4.60 |
| e1                   | -     | -    | 2.30 |
| L                    | 0.85  | 1.05 | 0.95 |
| Q                    | 0.84  | 0.94 | 0.89 |
| All Dimensions in mm |       |      |      |

### Suggested Pad Layout



| Dimensions | Value (in mm) |
|------------|---------------|
| C          | 2.30          |
| C1         | 6.40          |
| X          | 1.20          |
| X1         | 3.30          |
| Y          | 1.60          |
| Y1         | 1.60          |
| Y2         | 8.00          |